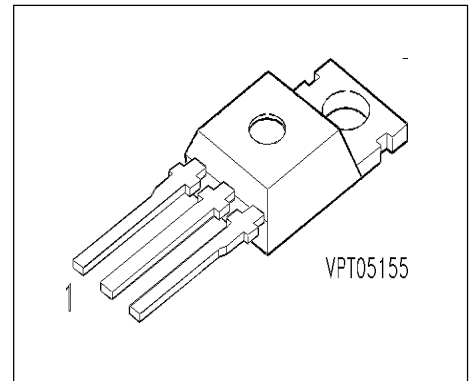


SIPMOS[®] Power Transistor

- N channel
- Enhancement mode



Pin 1	Pin 2	Pin 3
G	D	S

Type	V_{DS}	I_D	$R_{DS(on)}$	Package	Ordering Code
BUZ 80A	800 V	3 A	3 Ω	TO-220 AB	C67078-A1309-A3

Maximum Ratings

Parameter	Symbol	Values	Unit
Drain source voltage	V_{DS}	800	V
Drain-gate voltage $R_{GS} = 20 \text{ k}\Omega$	V_{DGR}	800	
Continuous drain current $T_C = 50 \text{ }^\circ\text{C}$	I_D	3	A
Pulsed drain current $T_C = 25 \text{ }^\circ\text{C}$	I_{Dpuls}	12	
Gate source voltage	V_{GS}	± 20	V
Power dissipation $T_C = 25 \text{ }^\circ\text{C}$	P_{tot}	75	W
Operating temperature	T_j	-55 + 150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 + 150	
Thermal resistance, chip case	R_{thJC}	≤ 1.67	K/W
Thermal resistance, chip to ambient	R_{thJA}	75	
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		55 / 150 / 56	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain- source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = 0.25\text{ mA}$, $T_j = 25\text{ }^{\circ}\text{C}$	$V_{(BR)DSS}$	800	-	-	V
Gate threshold voltage $V_{GS}=V_{DS}$, $I_D = 1\text{ mA}$	$V_{GS(th)}$	2.1	3	4	
Zero gate voltage drain current $V_{DS} = 800\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25\text{ }^{\circ}\text{C}$ $V_{DS} = 800\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 125\text{ }^{\circ}\text{C}$	I_{DSS}	- -	20 100	250 1000	μA
Gate-source leakage current $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	-	10	100	nA
Drain-Source on-resistance $V_{GS} = 10\text{ V}$, $I_D = 1.5\text{ A}$	$R_{DS(on)}$	-	2.7	3	Ω